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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claim 1 (currently amended): An MIM capacitor comprising:
a lower electrode comprising a plurality of metal layers including a top metal layer;

an upper electrode; and

a dielectric layer positioned between said lower electrode and said upper electrode,

wherein the ~~entire surface of the top metal layer is oxidized to form~~ includes an insulating metal oxide layer disposed on the entire surface thereof.

Claim 2 (original): An MIM capacitor according to Claim 1, wherein the top metal layer comprises a material selected from transition metals and alloys thereof which are capable of forming insulating layers by oxidation.

Claim 3 (original): An MIM capacitor according to Claim 1, wherein the top metal layer comprises titanium.

Claim 4 (original): An MIM capacitor according to Claim 1, wherein said dielectric layer comprises silicon nitride.

Claim 5 (original): An MIM capacitor according to Claim 4, wherein the surface of said dielectric layer is oxidized to form an oxidized silicon nitride layer.

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Claims 6-10 (canceled).

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Claim 11 (original): A microwave monolithic integrated circuit comprising an MIM capacitor as set forth in Claim 1.

Claim 12 (canceled).